

Switchmode Power Rectifiers

... Designed for use in switching power supplies, inverters and as free wheeling diodes. These state-of-the-art devices have the following features:

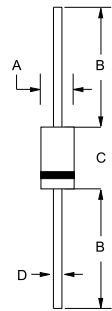
- * High Surge Capacity
- * Low Power Loss, High efficiency
- * Glass Passivated chip junctions
- * 150 °C Operating Junction Temperature
- * Low Stored Charge Majority Carrier Conduction
- * Low Forward Voltage , High Current Capability
- * Ultrafast 35 & 50 Nanosecond Recovery Time
- * Plastic Material used Carries Underwriters Laboratory Flammability Classification 94V-O

**ULTRA FAST
RECTIFIERS**

**2.0 AMPERES
50 -- 400 VOLTS**



DO-41



DIM	MILLIMETERS	
	MIN	MAX
A	2.00	2.70
B	25.40	---
C	4.10	5.20
D	0.70	0.90

CASE---
Transfer molded plastic

POLARITY---
Cathode indicated polarity band

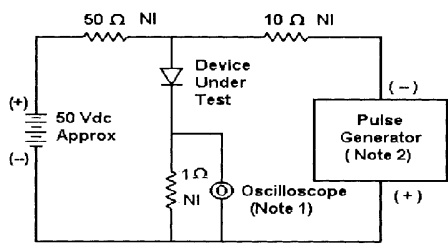
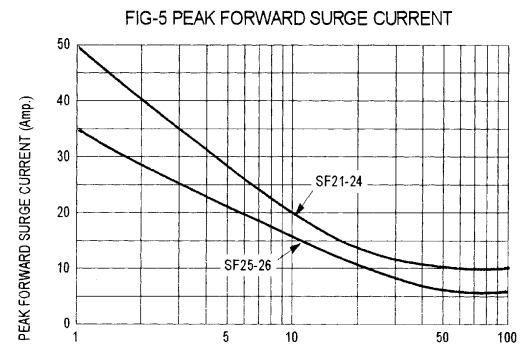
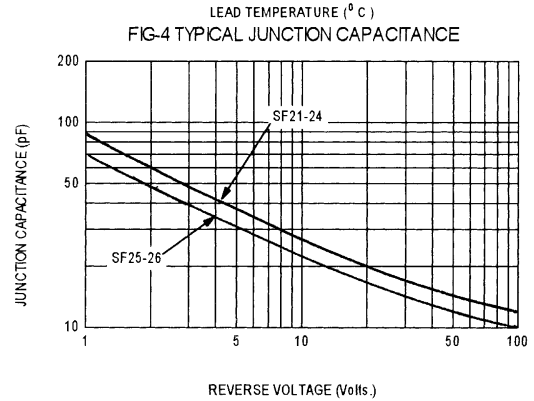
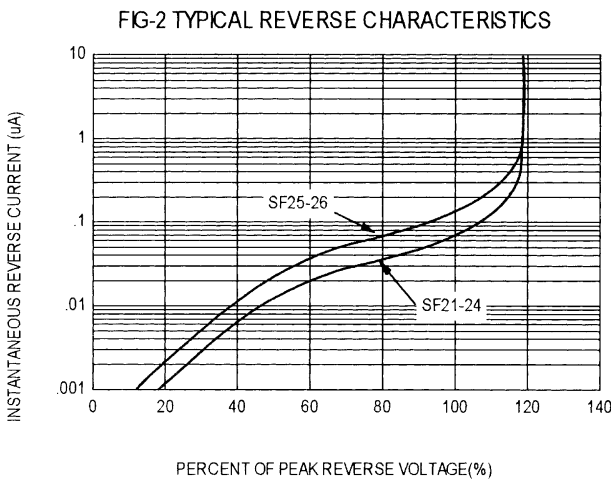
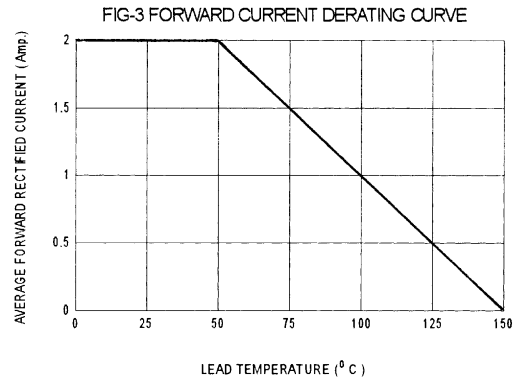
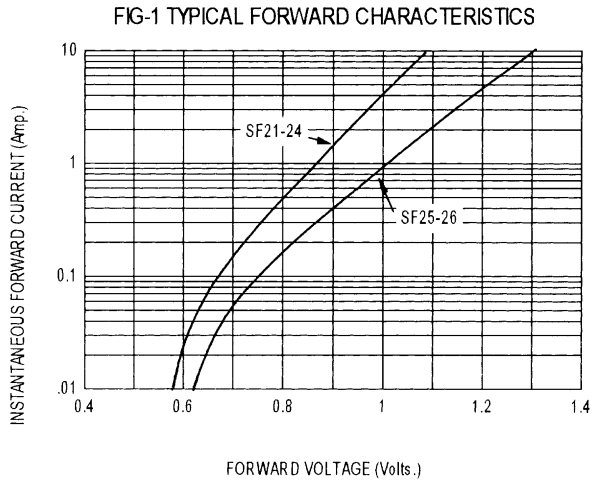
MAXIMUM RATINGS

Characteristic	Symbol	SF						Unit
		21	22	23	24	25	26	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	150	200	300	400	V
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	105	140	210	280	V
Average Rectifier Forward Current	I_O	2.0						A
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions halfwave, single phase, 60Hz)	I_{FSM}	50				35		A
Operating and Storage Junction Temperature Range	T_J, T_{stg}	- 65 to + 150						°C

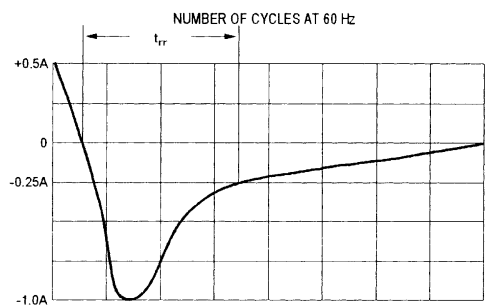
ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	SF						Unit
		21	22	23	24	25	26	
Maximum Instantaneous Forward Voltage ($I_F=2.0$ Amp, $T_C = 25$ °C)	V_F	0.95				1.30		V
Maximum Instantaneous Reverse Current (Rated DC Voltage, $T_C = 25$ °C) (Rated DC Voltage, $T_C = 125$ °C)	I_R	5.0				50		uA
Reverse Recovery Time ($I_F = 0.5$ A, $I_R = 1.0$, $I_{rr} = 0.25$ A)	T_{rr}	35				50		ns
Typical Junction Capacitance (Reverse Voltage of 4 volts & $f=1$ MHz)	C_P	40				35		pF

SF21 Thru SF26



- Notes:**
 1. Rise Time = 7 ns max. Input Impedance = 1 M Ω, 22 pF
 2. Rise Time = 10 ns max. Input Impedance = 50 Ω



Set time base for 10/20 ns/div

Fig-6 Reverse Recovery Time Characteristic and Test Circuit Diagram